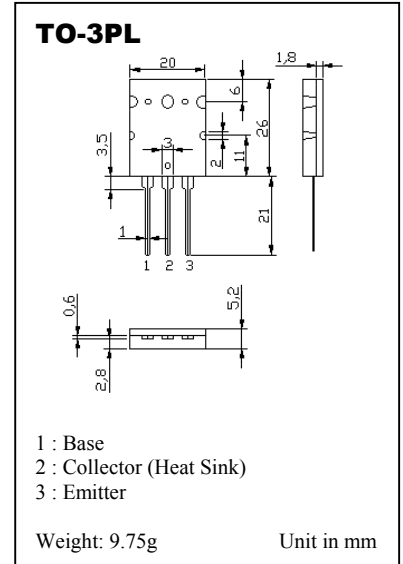


PNP SILICON TRIPLE DIFFUSED TRANSISTOR

...designed for power amplifier applications.

MAXIMUM RATINGS ($T_a = 25\text{ }^\circ\text{C}$)

Characteristic	Symbol	Value	Unit
Collector Base Voltage	V_{CB0}	-200	V
Collector Emitter Voltage	V_{CE0}	-200	V
Emitter Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-15	A
Base Current	I_B	-1.5	A
Collector power Dissipation $T_c = 25\text{ }^\circ\text{C}$	P_C	150	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ\text{C}$



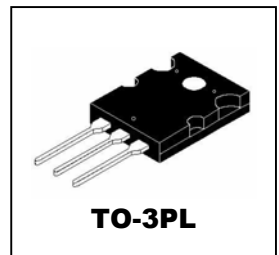
ELECTRICAL CHARACTERISTICS ($T_a = 25\text{ }^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I_{CB0}	$V_{CB} = -200V, I_E = 0$	-	-	-5	μA
Emitter Cutoff Current	I_{EB0}	$V_{EB} = -5V, I_C = 0$	-	-	-5	μA
Collector Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -50mA, I_B = 0$	-200	-	-	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -5V, I_C = -1A$	55	-	160	-
	$h_{FE(2)}$	$V_{CE} = -5V, I_C = -8A$	35	60	-	-
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10A, I_B = -1A$	-	-1.5	-3	V
Base Emitter Voltage	V_{BE}	$V_{CE} = -5V, I_C = -8A$	-	-1	-1.5	V
Transition Frequency	f_T	$V_{CE} = -5V, I_C = -1A$	-	25	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	470	-	pF

**PNP SILICON
TRIPLE DIFFUSED
TRANSISTOR**

Classification of $h_{FE(1)}$

Class	R	O
$h_{FE(1)}$	55 to 110	80 to 160



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